

November 2013

FQP65N06

N-Channel QFET[®] MOSFET 60 V, 65 A, 16 m Ω

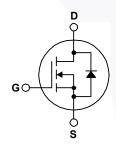
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 65 A, 60 V, $R_{DS(on)}$ = 16 m Ω (Max.) @ V_{GS} = 10 V, I_D = 32.5 A
- Low Gate Charge (Typ. 48 nC)
- Low Crss (Typ. 100 pF)
- · 100% Avalanche Tested
- · 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP65N06	Unit	
V _{DSS}	Drain-Source Voltage		60	V	
I _D	Drain Current - Continuous (T _C = 25°C))	65	Α	
	- Continuous (T _C = 100°C	C)	46.1	Α	
I _{DM}	Drain Current - Pulsed	(Note 1)	260	Α	
V_{GSS}	Gate-Source Voltage		± 25	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	650	mJ	
I _{AR}	Avalanche Current	(Note 1)	65	Α	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	15.0	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns	
P_{D}	Power Dissipation (T _C = 25°C)		150	W	
	- Derate above 25°C		1.00	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range	е	-55 to +175	°C	
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FQP65N06	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.00	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP65N06	FQP65N06	TO-220	Tube	N/A	N/A	50 units

Electrical	Characteristics	
Fiectrical	I Unaracteristics	

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		0.07		V/°C
I _{DSS}	Zoro Cata Valtaga Drain Current	V _{DS} = 60 V, V _{GS} = 0 V			1	μА
	Zero Gate Voltage Drain Current	V _{DS} = 48 V, T _C = 150°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10 V, I _D =32.5 A		0.012	0.016	Ω
g _{FS}	Forward Transconductance	V _{DS} = 25 V, I _D = 32.5 A		48		S
Dynam	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1850	2410	pF
^	0 1 10 "			700	0.4.0	_

Switching Characteristics

Output Capacitance

Reverse Transfer Capacitance

t _{d(on)}	Turn-On Delay Time	V _{DD} = 30 V, I _D = 32.5 A,		20	50	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		160	330	ns
t _{d(off)}	Turn-Off Delay Time			90	190	ns
t _f	Turn-Off Fall Time	(Note 4)	/	105	220	ns
Q_g	Total Gate Charge	V _{DS} = 48 V, I _D = 65 A,		48	65	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	A	12		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		19.5	/	nC

f = 1.0 MHz

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current				65	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				260	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 65 A			1.5	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_{S} = 65 \text{ A,}$		62		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		110		nC

 C_{oss}

 C_{rss}

- Notes: Notes: Notes: A Repetitive Rating: Pulse width limited by maximum junction temperature.
 2. L = 180 μ H, I_{AS} = 65 A, V_{DD} = 25 V, R_G = 25 Ω , starting T_J = 25°C.
 3. I_{SD} \leq 65 A, di/dt \leq 300 A/ μ s, V_{DD} \leq BV_{DSS}, starting T_J = 25°C.
 4. Essentially Independent of Operating Temperature.

700

100

910

130

pF

pF

Typical Characteristics

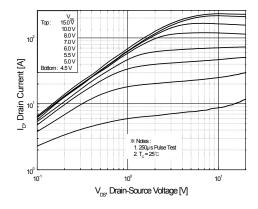


Figure 1. On-Region Characteristics

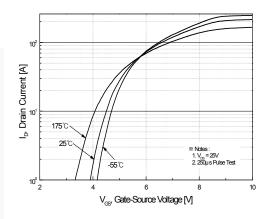


Figure 2. Transfer Characteristics

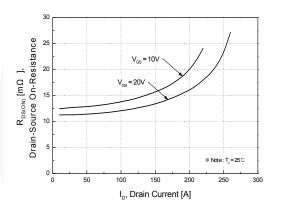


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

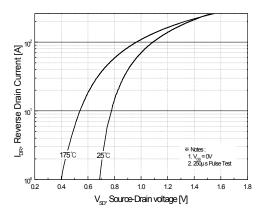


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

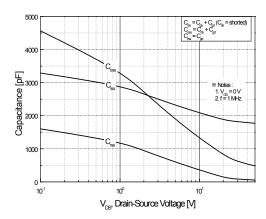


Figure 5. Capacitance Characteristics

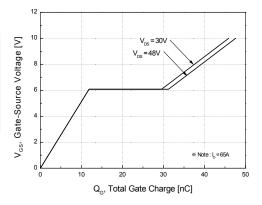


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

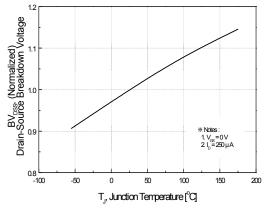


Figure 7. Breakdown Voltage Variation vs. Temperature

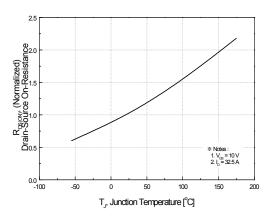


Figure 8. On-Resistance Variation vs. Temperature

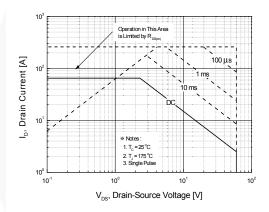


Figure 9. Maximum Safe Operating Area

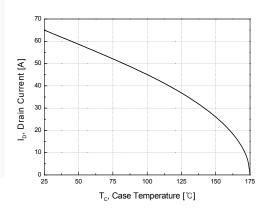


Figure 10. Maximum Drain Current vs. Case Temperature

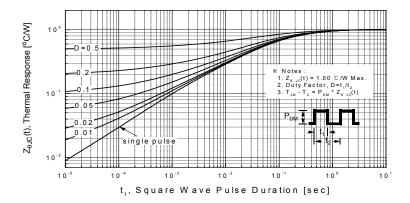


Figure 11. Transient Thermal Response Curve

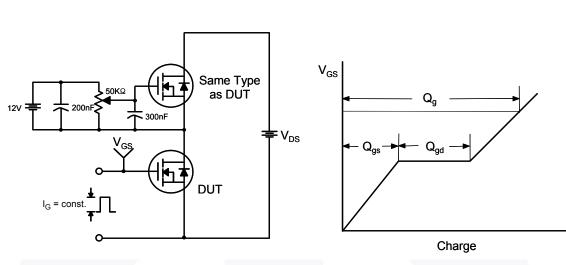


Figure 12. Gate Charge Test Circuit & Waveform

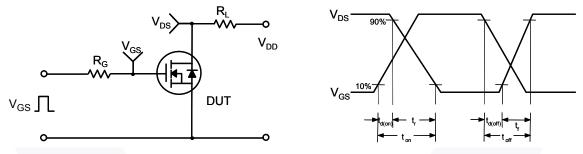


Figure 13. Resistive Switching Test Circuit & Waveforms

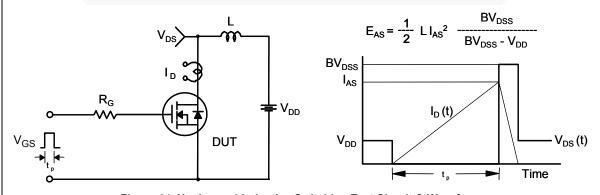
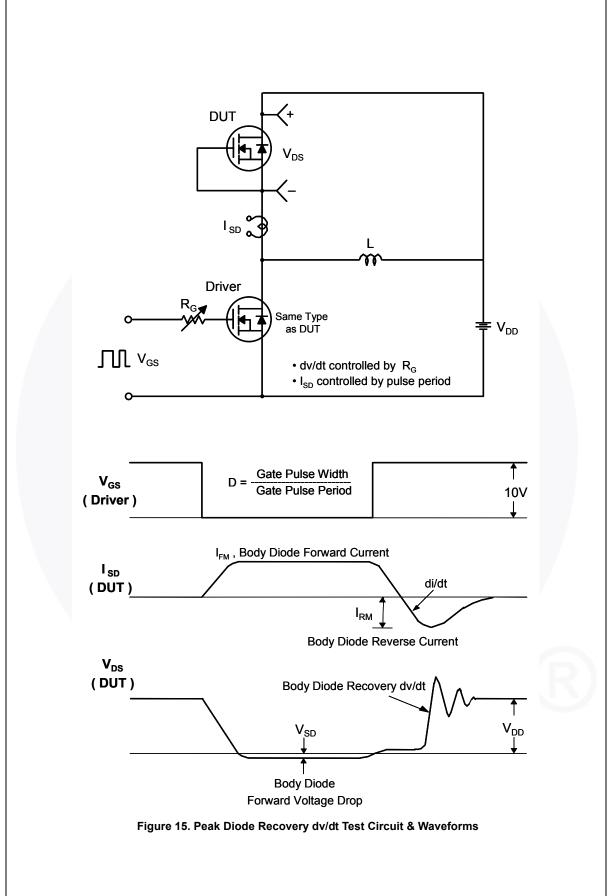
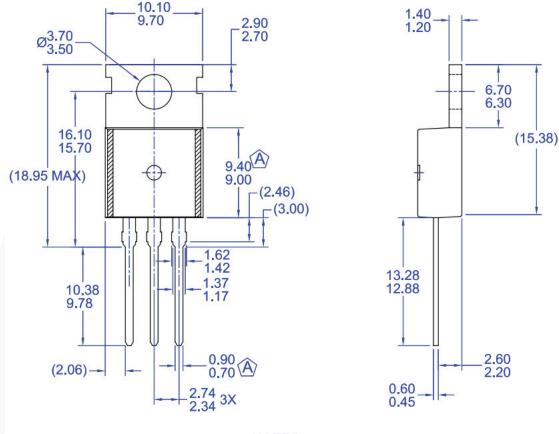


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions



4.70 4.30

9.80

NOTES:

- (A) CONFORMS TO JEDEC TO-220 VARIATION AB EXCEPT WHERE NOTED
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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